

SKNa 102



Stud Diode

Avalanche Diode

SKNa 102

Publish Data

Features

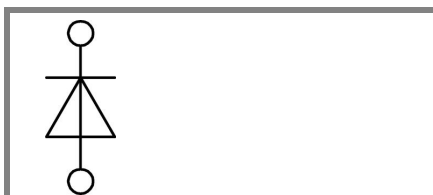
- Avalanche type reverse characteristic
- Reverse voltages up to 5000 V
- Hermetic metal case with ceramic insulator and extra long creepage distances
- Threaded stud ISO M12
- Cooling via heatsinks
- SKN: Anode to stud

Typical Applications

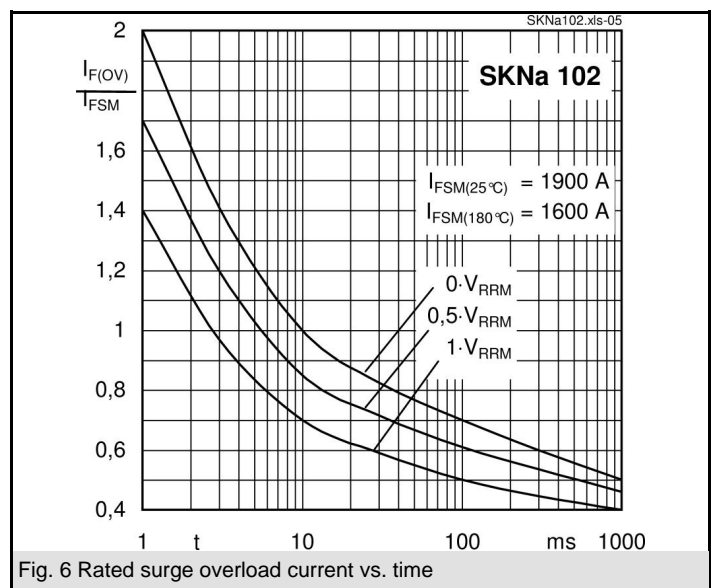
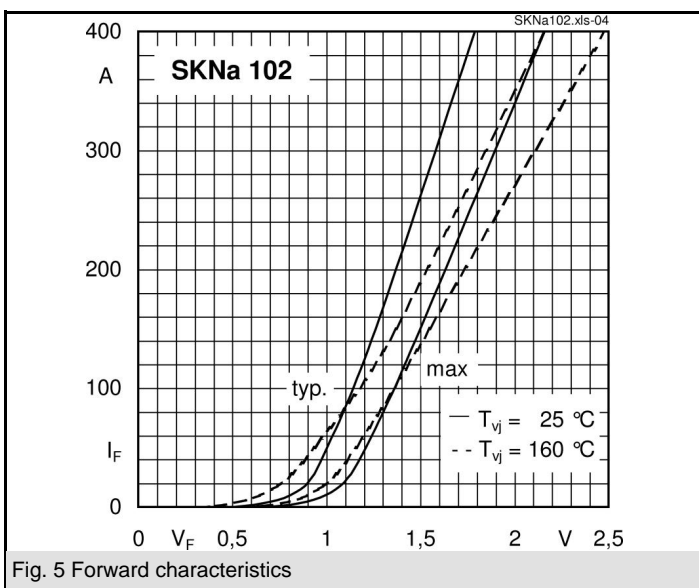
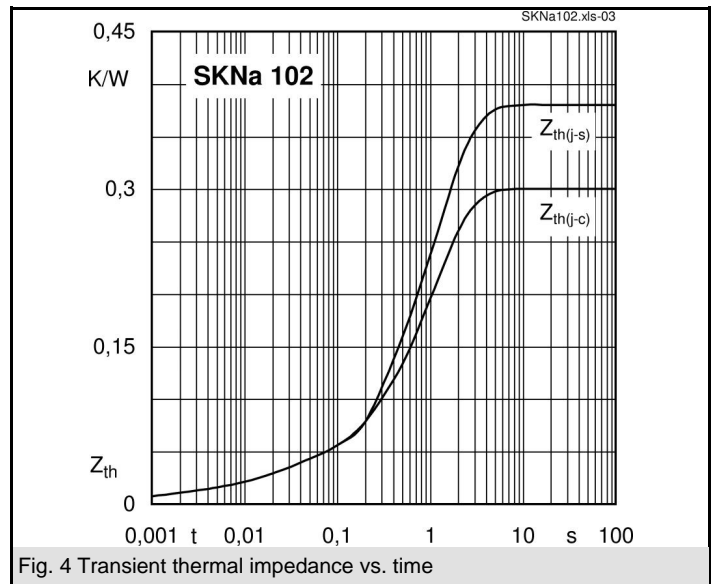
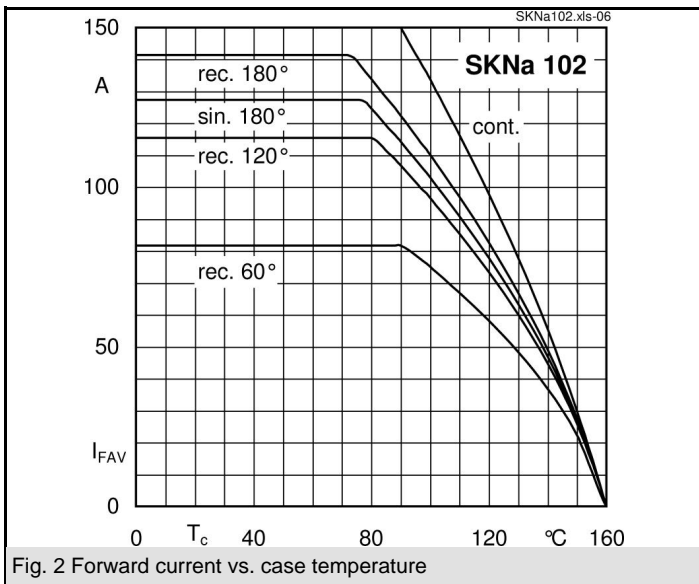
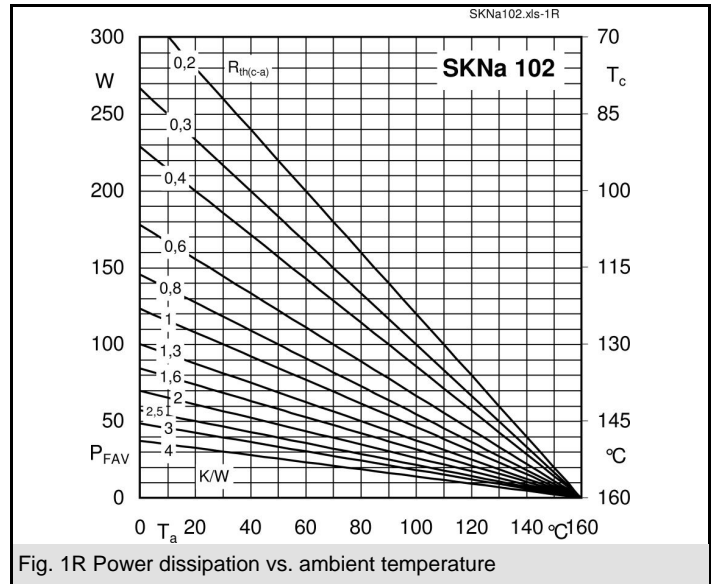
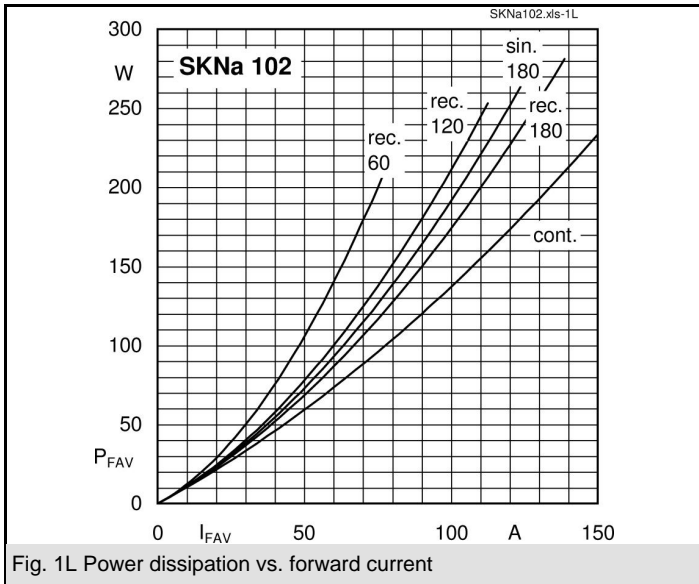
- High voltage rectifier diode for traction and heavy duty applications
- Series connections for high voltage applications
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes

$V_{(BR)min}$ V	$I_{FRMS} = 200$ A (maximum value for continuous operation) $I_{FAV} = 125$ A (sin. 180; $T_c = 80$ °C)	C_{max} μ F	R_{min} Ω
3600	SKNa 102/36		
4000	SKNa 102/40		
4200	SKNa 102/42		
4500	SKNa 102/45		
4600	SKNa 102/46		
4800	SKNa 102/48		
5000	SKNa 102/50		

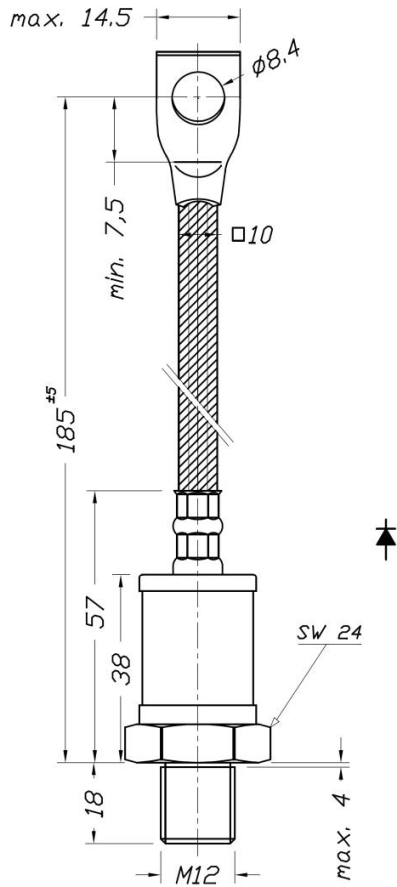
Symbol	Conditions	Values	Units
I_{FAV}	sin. 180 ; $T_c = 80$ (102) °C	125 (100)	A
I_D	K 1,1; $T_a = 45$ °C; B2 / B6	114 / 162	A
	K 1,1F; $T_a = 35$ °C; B2 / B6	189 / 266	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms	1900	A
	$T_{vj} = 160$ °C; 10 ms	1600	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	18000	A ² s
	$T_{vj} = 160$ °C; 8,3 ... 10 ms	12500	A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 300$ A	max. 1,9	V
$V_{(TO)}$	$T_{vj} = 150$ °C	max. 1	V
r_T	$T_{vj} = 150$ °C	max. 3,7	m Ω
I_{RD}	$T_{vj} = 25$ °C; $V_{RD} = V_{(BR)min}$	max. 1000	μ A
	$T_{vj} = 160$ °C; $V_{RD} = V_{(BR)min}$	max. 15	mA
P_{RSM}	$T_{vj} = 160$ °C; $t_p = 10$ μ s	36	kW
$R_{th(j-c)}$		0,3	K/W
$R_{th(c-s)}$		0,08	K/W
T_{vj}		- 40 ... + 160	°C
T_{stg}		- 40 ... + 160	°C
V_{isol}		-	V~
M_s	to heatsink	10	Nm
		90	lb.in.
a		5 * 9,81	m/s ²
m	approx.	110	g
Case		E 44	



SKN



Dimensions in mm



CASE E 44 (IEC 60191: A 9 MA modified)

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